



#### **N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = 25°C
	$55m\Omega$ @ $V_{GS} = 4.5V$	4.0A
20V	$70m\Omega @ V_{GS} = 2.5V$	3.5A
	$90m\Omega @ V_{GS} = 1.8V$	3.1A
	130mΩ @ V <sub>GS</sub> = 1.5V	2.5A

## **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

## **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

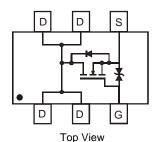
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)





SOT26

Top View



Internal Schematic

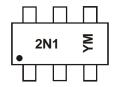
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN2100UDM-7	SOT26	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com...

## **Marking Information**



2N1 = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	201	1 20	)12	20	13	2014	2015	2016	2017
Code	U	V	W	Х	Υ		Z	ŀ	Д	В	С	D	Е
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jı	ıl	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	,	8	9	0	N	D



## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units			
Drain-Source Voltage	$V_{DSS}$	20	V			
Gate-Source Voltage	$V_{GSS}$	±8	V			
Continuous Drain Current (Note 6) \/ 4.5\/	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	4.0 3.1	А	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	t<10s	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	4.5 3.5	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	13	А			
Maximum Body Diode Continuous Current	I <sub>S</sub>	1.5	A			

## **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Total Bower Dissination (Note 5)	T <sub>A</sub> = 25°C		1	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = 70°C	$P_{D}$	0.6	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	Р	127	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	91		
Total Dawer Dissipation (Note C)	T <sub>A</sub> = 25°C	<u> </u>	1.5	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = 70°C	P <sub>D</sub>	0.9		
Thormal Bosistanos, Junation to Ambient (Note 6)	Steady state	D	85		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	63	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3.1		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

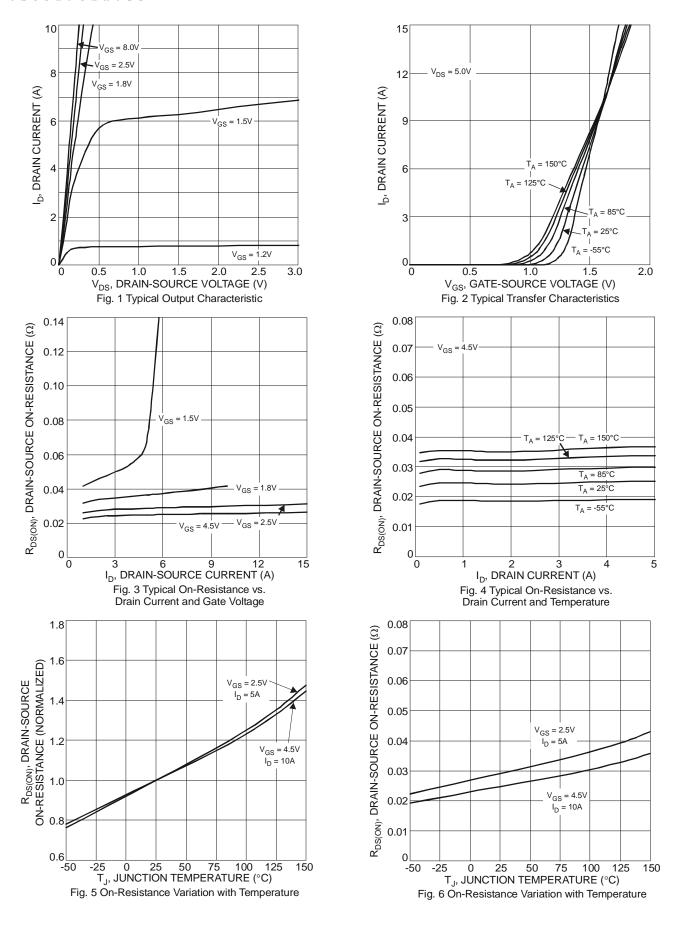
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
			32	55		$V_{GS} = 4.5V, I_D = 6A$
Static Drain-Source On-Resistance		_	43	70	mΩ	$V_{GS} = 2.5V, I_D = 4.0A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		56	90		$V_{GS} = 1.8V, I_D = 1.5A$
		_	80	130		$V_{GS} = 1.5V, I_D = 1.0A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	8	_	S	$V_{DS} = 10V, I_{D} = 6A$
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.1	V	$V_{GS} = 0V, I_{S} = 2A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>		555	_	рF	V 40V V 0V
Output Capacitance	Coss		112		рF	$V_{DS} = 10V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	Crss		84		pF	1 = 1.0101112
Total Gate Charge	Qg		8.8		nC	V 40V V 45V
Gate-Source Charge	Qgs	_	1.4	_	nC	$V_{DS} = 10V, V_{GS} = 4.5V,$
Gate-Drain Charge	$Q_{gd}$	_	3	_	nC	$I_D = 6.5A$
Turn-On Delay Time	t <sub>D(on)</sub>		53	_	ns	
Turn-On Rise Time	t <sub>r</sub>		78	_	ns	$V_{DS} = 10V, I_{D} = 1.0A$
Turn-Off Delay Time	t <sub>D(off)</sub>		561		ns	$V_{GS} = 4.5V$ , $R_G = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	234	_	ns	

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
  Short duration pulse test used to minimize self-heating effect
  Guaranteed by design. Not subject to production testing







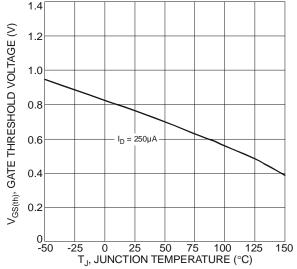
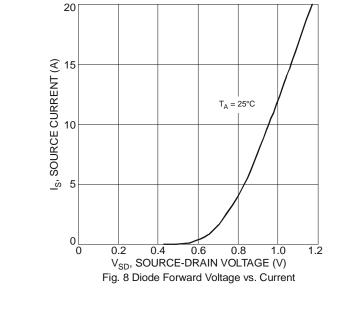
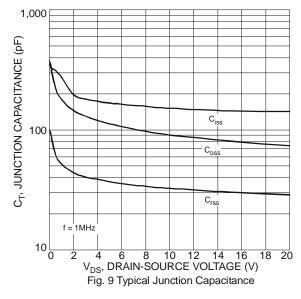
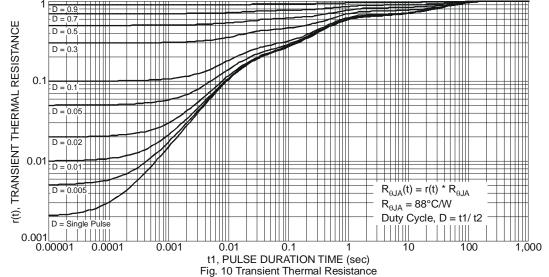


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

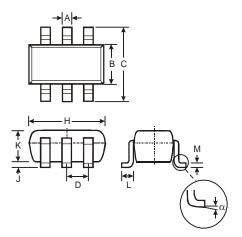






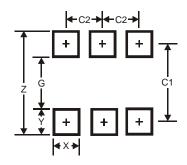


# **Package Outline Dimensions**



SOT26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	_	_	0.95			
Н	2.90	3.10	3.00			
7	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	0°	8°	_			
All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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